

### ABSTRACT OF THE DISCLOSURE

An inventive semiconductor device includes: an interlevel dielectric film **204** provided on a semiconductor substrate **101**; and interconnects **208a** and **208c** buried in the interlevel dielectric film **204** and electrically connected to the semiconductor substrate **101**.

- 5 An MIM capacitor **201** includes: first and second electrodes **208b** and **214b** each made of a metal; and a capacitive insulating film **210** of a dielectric. The first electrode **208b** is buried in the interlevel dielectric film **204**. The capacitive insulating film **210** is provided on the first electrode **208b**. The second electrode **214b** is a metal layer provided to face the first electrode **208b** with the capacitive insulating film **210** interposed therebetween.